

# Rajab Yahyazadeh

## List of Publications by Year in descending order

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Version: 2024-02-01

18  
papers

42  
citations

1937685

4  
h-index

1872680

6  
g-index

18  
all docs

18  
docs citations

18  
times ranked

36  
citing authors

#	ARTICLE	IF	CITATIONS
1	Stability analysis of FGM microgripper subjected to nonlinear electrostatic and temperature variation loadings. <i>Science and Engineering of Composite Materials</i> , 2016, 23, 199-207.	1.4	13
2	The effects of depletion layer on negative differential conductivity in AlGaIn/GaN high electron mobility transistor. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 33, 77-82.	2.7	9
3	Numerical modeling of electronic and electrical characteristics of InGaIn/GaN multiple quantum well solar cells. <i>Journal of Photonics for Energy</i> , 2020, 10, .	1.3	5
4	Effect of hydrostatic pressure on the photocurrent density of $\text{InGaIn/GaN}$ multiple quantum well solar cells. <i>Indian Journal of Physics</i> , 2022, 96, 2815-2826.	1.8	4
5	Effect of temperature on the transconductance of AlGaIn/GaN high electron mobility transistors (HEMT). <i>International Journal of Academic Research</i> , 2013, 5, 78-86.	0.1	2
6	Effect of Hydrostatic Pressure and Temperature on Quantum Confinement of AlGaIn/GaN HEMTs. <i>Journal of Science and Technology</i> , 2021, 13, .	0.2	2
7	Optical gain of AlGaIn/GaN multiquantum well laser diode influenced by hydrostatic pressure. <i>Journal of Nanophotonics</i> , 2021, 15, .	1.0	2
8	Effect of hydrostatic pressure on the radiative current density of InGaIn/GaN multiple quantum well light emitting diodes. <i>Optical and Quantum Electronics</i> , 2021, 53, 1.	3.3	2
9	The effect of depletion layer on the cut off frequency of AlGaIn/GaN high electron mobility transistors. , 2010, , .		1
10	Effect of Temperature on the Total Mobility of AlGaIn/GaN High Electron Mobility Transistors. <i>ECS Transactions</i> , 2014, 60, 1051-1055.	0.5	1
11	Numerical Optimization for Source-Drain Channel Resistance of AlGaIn/GaN HEMTs. <i>Journal of Science and Technology</i> , 2019, 11, .	0.2	1
12	Effect of temperature on the electronic current of two dimensional quantum well in AlGaIn/GaN high electron mobility transistors (HEMT). , 2010, , .		0
13	Effect of AlGaIn Barrier Thickness on the Noise of AlGaIn/GaN High Electron Mobility Transistors. <i>ECS Transactions</i> , 2011, 34, 67-73.	0.5	0
14	Effect of AlGaIn Barrier Thickness on the Cut Off Frequency of AlGaIn/GaN High Electron Mobility Transistors. <i>ECS Transactions</i> , 2012, 44, 165-172.	0.5	0
15	Effect of AlGaIn barrier thickness on the cut off frequency of AlGaIn/GaN High electron mobility transistors. <i>International Journal of Academic Research</i> , 2012, 4, 72-78.	0.1	0
16	Analytical-Numerical Model for the Total Mobility of AlGaIn/GaN High Electron Mobility Transistors. <i>ECS Transactions</i> , 2012, 44, 49-55.	0.5	0
17	Effect of AlGaIn Barrier Thickness on the Transconductance of AlGaIn/GaN High Electron Mobility Transistors. <i>ECS Transactions</i> , 2014, 60, 57-61.	0.5	0
18	Effect of Temperature on the Cut off Frequency of AlGaIn/GaN High Electron Mobility Transistors. <i>ECS Transactions</i> , 2014, 60, 1021-1026.	0.5	0